## AM3531C

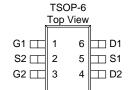
## **Analog Power**

# N & P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
30	$0.058 @ V_{GS} = 4.5V$	3.7			
50	$0.082 @ V_{GS} = 2.5V$	3.1			
-26.5	$0.112 @ V_{GS} = -4.5V$	-2.7			
	$0.172 @ V_{GS} = -2.5V$	-2.2			





N-Channel MOSFET

D

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)								
Parameter			N-Channel	P-Channel	Units			
Drain-Source Voltage		V <sub>DS</sub>	30	-26.5	V			
Gate-Source Voltage			±12	±12	v			
	$T_A=25^{\circ}C$	т	3.7	-2.7	А			
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	2.9	-2.1				
Pulsed Drain Current <sup>b</sup>			8	-8				
Continuous Source Current (Diode Conduct	Is	1.05	-1.05	Α				
	$T_A=25^{\circ}C$		1.	W				
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	rр	0.	vv				
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to	°C				

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Тур	Max	Тур	Max	Unit
	t <= 10 sec	D	93	110	93	110	<sup>0</sup> C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	R <sub>thJA</sub>	130	150	130	150	°C/W

Notes

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- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Description			OTED)				<b>.</b>	
Parameter	Symbol	Test Conditions	Ch	Ch Min T		Max	Unit	
Static								
Gate-Threshold Voltage	V	$V_{GS} = V_{DS}, I_D = 250 \text{ uA}$	N	0.6			v	
	$V_{GS(th)}$	$V_{GS} = V_{DS}$ , $I_D = -250 \text{ uA}$	Р	-0.6			v	
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = 12 V$	N P			100	uA	
	000	$V_{DS} = 0 V, V_{GS} = -12 V$ $V_{DS} = 21 V, V_{GS} = 0 V$	P N			-100		
	÷	$V_{DS} = -21 V, V_{GS} = 0 V$ $V_{DS} = -21 V, V_{GS} = 0 V$	P			-1	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 21 \text{ V}, V_{GS} = 0 \text{ V}, T_{I} = 55^{\circ}\text{C}$	N			10		
		$V_{DS} = -24 \text{ V}, V_{CS} = 0 \text{ V}, T_{I} = 55^{\circ}\text{C}$	Р			-10	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$\frac{V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}}{V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}}$	Ν	5			А	
	*D(on)		Р	-5		0.050	A	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 V, I_D = 3.7 A$	N P			0.058	-	
		$V_{GS} = -4.5 \text{ V}, \text{ ID} = 3.1 \text{ A}$ $V_{GS} = 2.5 \text{ V}, \text{ ID} = 2.7 \text{ A}$	r N			0.112	Ω	
		$V_{GS} = -2.5 V, I_D = -2.7 A$ $V_{GS} = -2.5 V, I_D = -2.2 A$	P			0.00		
Forward Tranconductance <sup>A</sup>	a	$V_{DS} = 5 V, I_{D} = 3.7 A$	N		10		S	
Forward I ranconductance	g <sub>fs</sub>	$V_{\rm DS}^{\rm BS} = -5$ V, $I_{\rm D}^{\rm C} = 3.1$ A	Р		5		3	
Diode Forward Voltage <sup>A</sup>	V <sub>SD</sub>	$I_{\rm S} = 1.05 \text{ A}, V_{\rm GS} = 0 \text{ V}$	N		0.80		S	
-	· SD	$I_{\rm S} = -1.05 \text{ A}, V_{\rm GS} = 0 \text{ V}$	Р		-0.83		5	
Dynamic <sup>b</sup>								
Total Gate Charge	Qg	N-Channel	N P		6.3			
	₹5				3.8		4	
Gate-Source Charge	Qgs	$V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 2.7A$	N P		0.9		nC	
	Qgd	P-Channel	N		1.9			
Gate-Drain Charge		$V_{DS}$ =-15V, $V_{GS}$ =-4.5V, $I_{D}$ =-3.1A			1.5			
			P N		5			
Turn-On Delay Time	td(on)	N-Chaneel	Р		5			
	tr	$V_{\text{DD}}$ =15V, $V_{\text{GS}}$ =4.5V, $I_{\text{D}}$ =1A ,	N		12			
Rise Time		$R_{\text{gen}}=15\Omega$ ,	Р		15		nS	
Turn-Off Delay Time	td(off)	P-Channel	N		13		115	
	<b>cu</b> (01)	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A	P		20			
Falls Time	tr	$R_{GEN}=15\Omega$	N P		$\frac{7}{20}$	L		

a. Pulse test:  $PW \le 300$  us duty cycle  $\le 2\%$ .

b. Guaranteed by design, not subject to production testing.

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